

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7524	(257/680,686,748,750,758,777).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:26
L2	0	("1ands18").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:27
L3	0	("1ands18").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:27
L4	34137	(die chip) near3 (depress\$4 aperture cavity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 09:27
L5	344	1 and L4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:29
L6	344	4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:29
L7	3	l6 and insulat\$3 adj layer with (first near conductive adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 09:30
S1	1	10/624680	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 09:22
S2	36113	substrate with (depress\$4 aperture)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:05

S3	4493	S2 and conductive near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:06
S4	194023	(die chip device) near5 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:07
S5	1032	S3 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:13
S6	2689	insulat\$3 near layer near2 first near conductive adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:13
S7	14	insulat\$3 near layer near2 first near conductive adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:15
S8	0	S5 and S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:14
S9	1	S5 and insul\$3 adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:15
S10	600	S5 and insulat\$3 adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:15
S11	0	insulat\$3 adj layer near5 first near conductive adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:15
S12	3629	insulat\$3 adj layer with (first near conductive adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 09:30

S13	2857	insulat\$3 adj layer near5 (first near conductive adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:16
S14	25	S5 and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:17
S15	60283	substrate with (depress\$4 aperture cavity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:06
S16	37562	substrate near5 (depress\$4 aperture cavity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:06
S17	43121	(die chip) near5 (depress\$4 aperture cavity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:06
S18	34117	(die chip) near3 (depress\$4 aperture cavity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:07
S19	14	(("6709898") or ("5073814") or ("5524339") or ("6271469") or ("6403463") or ("6555906") or ("6274391")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/30 17:46
S20	0	S19 and pcb	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/30 17:46
S21	5	S19 and circuit near board	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/30 17:46